

CMOS Dual 2-Wide 2-Input AND-OR-INVERT Gate

High-Voltage Types (20-Volt Rating)

■ CD4085 contains a pair of AND-OR-INVERT gates, each consisting of two 2-input AND gates driving a 3-input NOR gate. Individual inhibit controls are provided for both A-O-I gates.

The CD4085B types are supplied in 14-lead dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

Features:

- Medium-speed operation — $t_{PHL} = 90$ ns; $t_{PLH} = 125$ ns (typ.) at 10 V
- Individual inhibit controls
- Standardized symmetrical output characteristics
- 100% tested for quiescent current at 20 V
- Maximum input current of $1 \mu\text{A}$ at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (over full package-temperature range):
 - 1 V at $V_{DD} = 5$ V
 - 2 V at $V_{DD} = 10$ V
 - 2.5 V at $V_{DD} = 15$ V
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

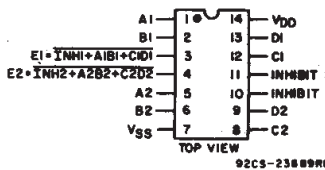
MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD}) Voltages referenced to V_{SS} Terminal	-0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS	-0.5V to $V_{DD} + 0.5$ V
DC INPUT CURRENT, ANY ONE INPUT	± 10 mA
POWER DISSIPATION PER PACKAGE (P_D):	
For $T_A = -55^\circ\text{C}$ to $+100^\circ\text{C}$	500 mW
For $T_A = +100^\circ\text{C}$ to $+125^\circ\text{C}$	Derate Linearity at 12 mW/°C to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR $T_A = \text{FULL PACKAGE-TEMPERATURE RANGE (All Package Types)}$	100 mW
OPERATING-TEMPERATURE RANGE (T_A)	-55°C to $+125^\circ\text{C}$
STORAGE TEMPERATURE RANGE (T_{stg})	-65°C to $+150^\circ\text{C}$
LEAD TEMPERATURE (DURING SOLDERING):	
At distance $1/16 \pm 1/32$ inch (1.59 ± 0.79 mm) from case for 10s max	$+265^\circ\text{C}$

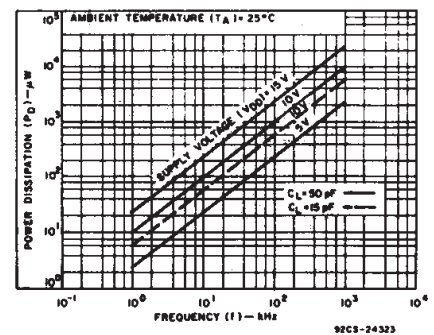
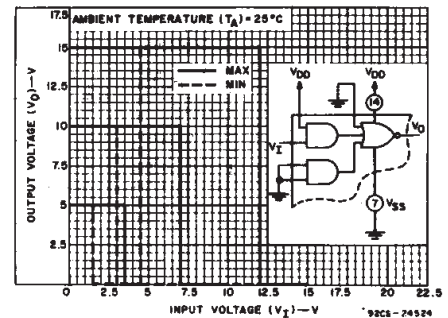
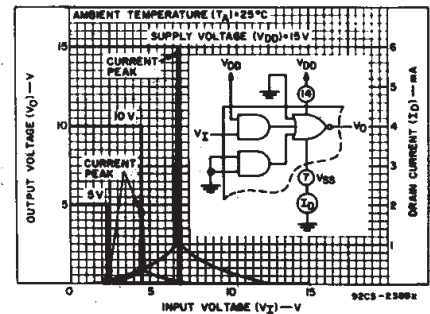
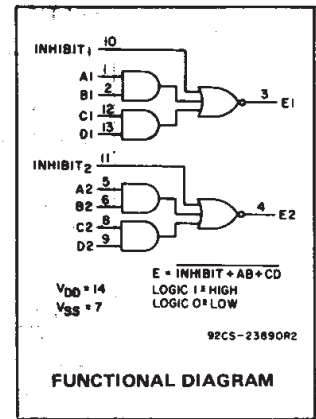
RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	Min.	Max.	
Supply-Voltage Range (For $T_A = \text{Full Package-Temperature Range}$)	3	18	V



Terminal Assignment



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STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V _O (V)	V _{IN} (V)	V _{DD} (V)	-55	-40	+85	+125	+25			
								Min.	Typ.	Max.	
Quiescent Device Current I _{DD} Max.	-	0,5	5	1	1	30	30	-	0.02	1	μA
	-	0,10	10	2	2	60	60	-	0.02	2	
	-	0,15	15	4	4	120	120	-	0.02	4	
	-	0,20	20	20	20	600	600	-	0.04	20	
Output Low (Sink) Current, I _{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	-	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	-	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	-	
	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	-	
Output High (Source) Current, I _{OH} Min.	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	-	mA
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	-	
	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	-	
	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	-	
Output Voltage: Low-Level, V _{OL} Max.	-	0,5	5	0.05				-	0	0.05	V
	-	0,10	10	0.05				-	0	0.05	
	-	0,15	15	0.05				-	0	0.05	
Output Voltage: High-Level, V _{OH} Min.	-	0,5	5	4.95				4.95	5	-	V
	-	0,10	10	9.95				9.95	10	-	
	-	0,15	15	14.95				14.95	15	-	
Input Low Voltage, V _{IL} Max.	0.5, 4.5	-	5	1.5				-	-	1.5	V
	1.9	-	10	3				-	-	3	
	1.5, 13.5	-	15	4				-	-	4	
Input High Voltage, V _{IH} Min.	0.5, 4.5	-	5	3.5				3.5	-	-	V
	1.9	-	10	7				7	-	-	
	1.5, 13.5	-	15	11				11	-	-	
Input Current, I _{IN} Max.	-	0,18	18	±0.1	±0.1	±1	±1	-	±10 ⁻⁵	±0.1	μA

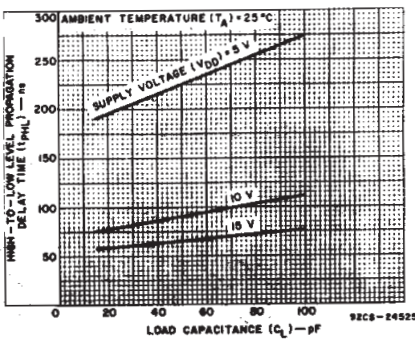


Fig. 4 - Typical data high-to-low level propagation delay time vs. load capacitance.

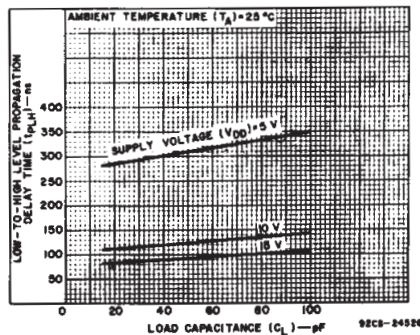


Fig. 5 - Typical data low-to-high level propagation delay time vs. load capacitance.

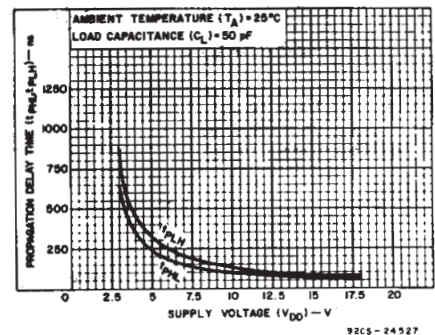


Fig. 6 - Typical data propagation delay time vs. supply voltage.

CD4085B Types

DYNAMIC ELECTRICAL CHARACTERISTICS at $T_A = 25^\circ\text{C}$; Input $t_r, t_f = 20 \text{ ns}$, $C_L = 50 \text{ pF}$, $R_L = 200 \text{ k}\Omega$

CHARACTERISTIC	CONDITIONS	LIMITS		UNITS
		V_{DD} V	Typ.	
Propagation Delay Time (Data): High-to-Low Level, t_{PHL}	5	225	450	ns
	10	90	180	
	15	65	130	
Low-to-High Level, t_{PLH}	5	310	620	ns
	10	125	250	
	15	90	180	
Propagation Delay Time (Inhibit): High-to-Low Level, t_{PHL}	5	150	300	ns
	10	60	120	
	15	40	80	
Low-to-High Level, t_{PLH}	5	250	500	ns
	10	100	200	
	15	70	140	
Transition Time, t_{THL}, t_{TLH}	5	100	200	ns
	10	50	100	
	15	40	80	
Input Capacitance, C_{IN}	Any Input	5	7.5	pF

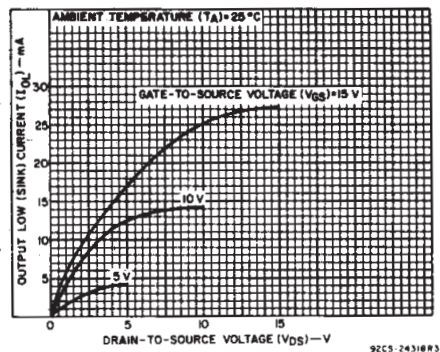


Fig. 7 - Typical output low (sink) current characteristics.

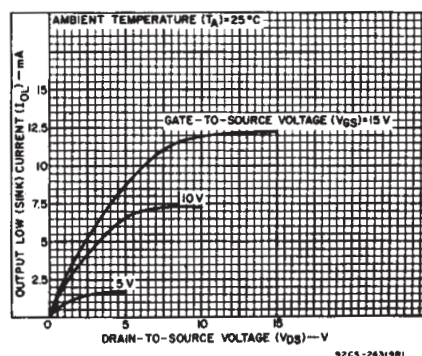


Fig. 8 - Minimum output low (sink) current characteristics.

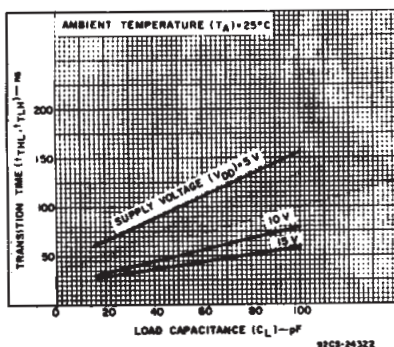


Fig. 9 - Typical transition time vs. load capacitance.

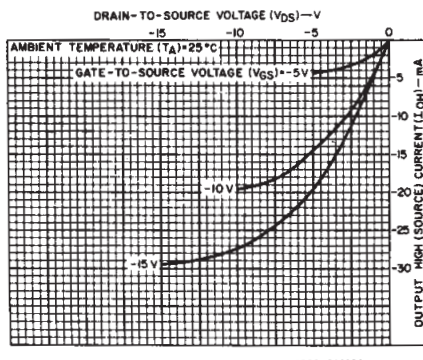


Fig. 10 - Typical output high (source) current characteristics.

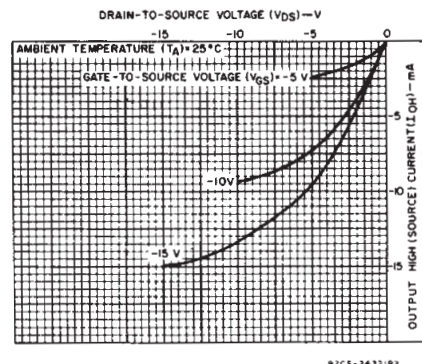


Fig. 11 - Minimum output high (source) current characteristics.

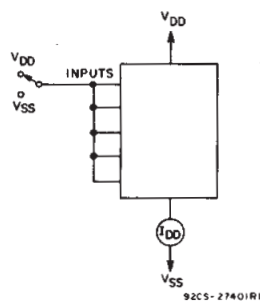


Fig. 12 - Quiescent device current test circuit.

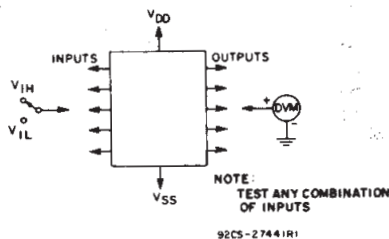


Fig. 13 - Input voltage test circuit.

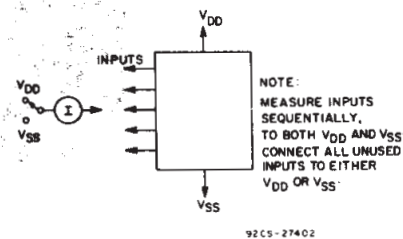


Fig. 14 - Input current test circuit.

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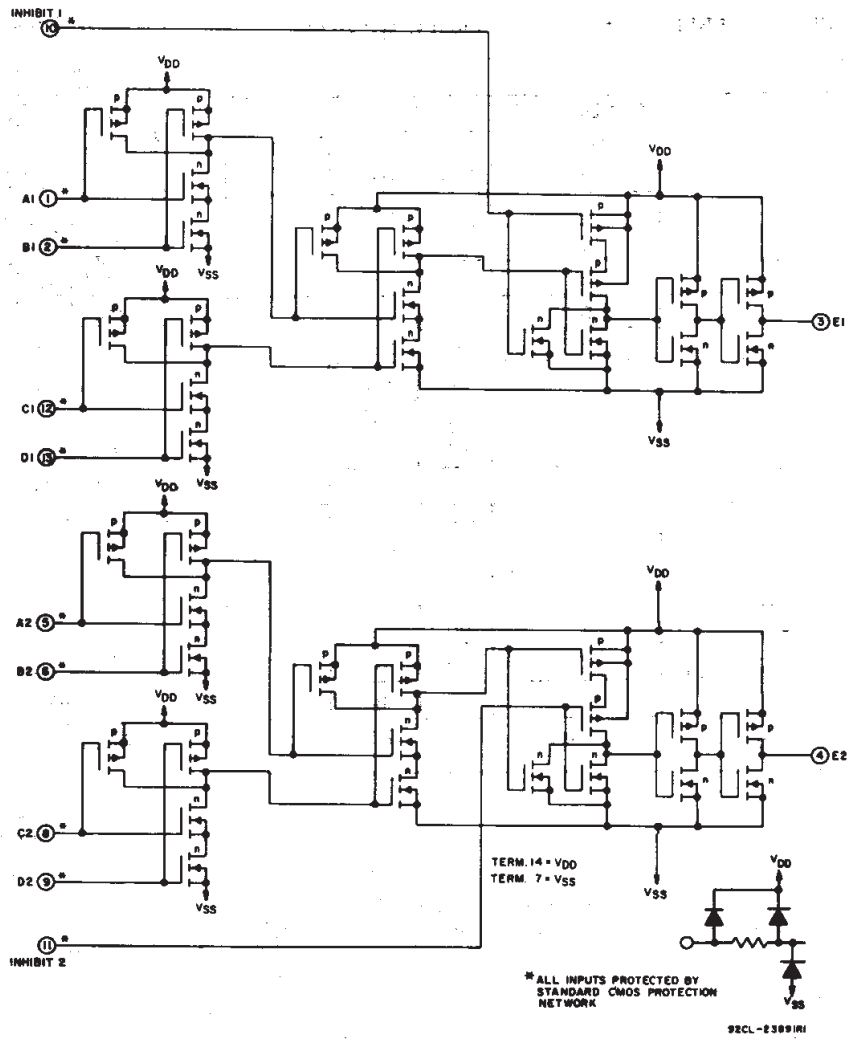
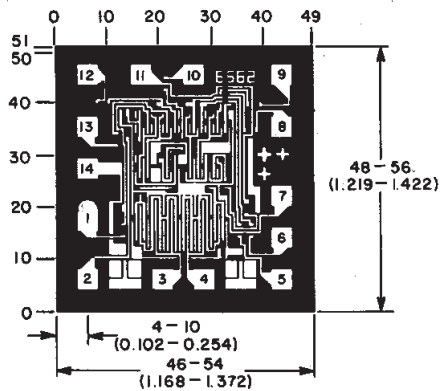


Fig. 15 - CD4085 schematic diagram.



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

Dimensions and Pad Layout for CD4085BH.

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